

BYV10MD-650P

Ultrafast power diode Rev.01 - 27 October 2022

Product data sheet

1. General description

Ultrafast power diode in a TO252 (DPAK) plastic package.



2. Features and benefits

- Low leakage current
- Low thermal resistance
- Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage				650		V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 89 °C; Fig. 1; Fig. 2; Fig. 3		10			A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 89 °C; square-wave pulse		20			A
I _{FSM} non-repetitive peak forward current		t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		50		A	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		55		А	
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.90	2.60	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.50	2.20	V
Dynamic	characteristics						
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 200 A/μs; T _j = 25 °C; <u>Fig. 7</u>		-	18	-	ns

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	n.c.	not connected		К-Ң-А	
2	K	cathode [1]		001aaa020	
3	A	anode			
mb	К	mounting base; connected to cathode			

[1] It is not possible to connect to pin 2 of the TO252 package.

6. Ordering information

Table 3. Ordering information								
Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date		
BYV10MD-650P	TO252	BYV10MD-650PJ	Reel	2500	TO252d	07-Sep-2022		

7. Marking

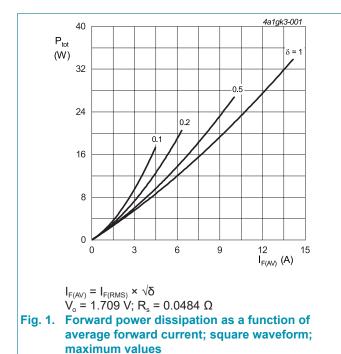
Table 4. Marking codes						
Type number	Marking codes					
BYV10MD-650P	BYV10MD 650P					

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{RRM}	repetitive peak reverse voltage			650	V
V_{RWM}	crest working reverse voltage			650	V
V _R	reverse voltage	DC		650	V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 89 °C; Fig. 1; Fig. 2; Fig. 3		10	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _{mb} ≤ 89 °C; square-wave pulse		20	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		50	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		55	А
T _{stg}	storage temperature			-65 to 175	°C
T_{j}	junction temperature			-65 to 175	°C



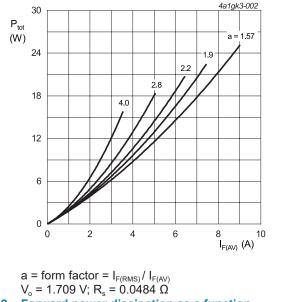
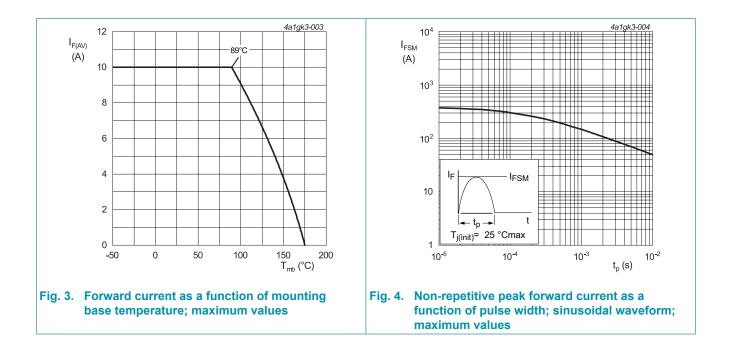


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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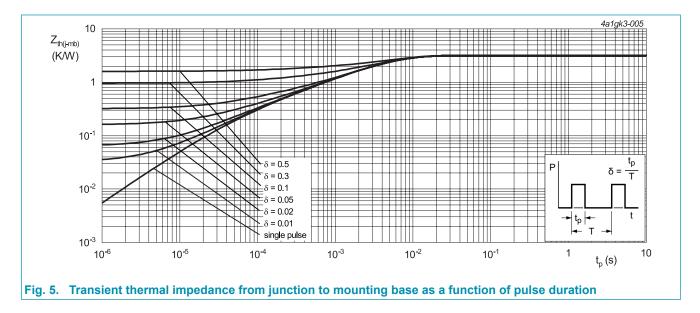
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9. Thermal characteristics

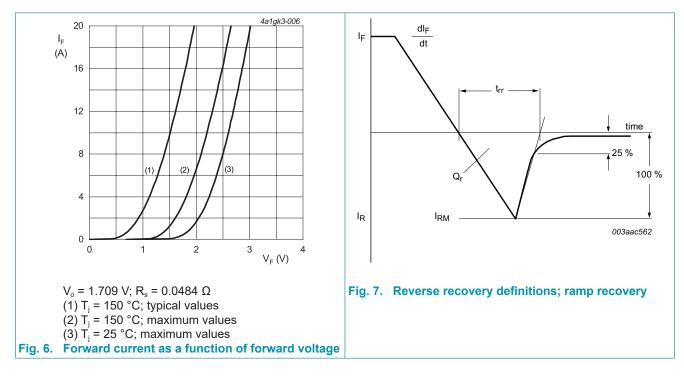
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	-	3.2	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	[2]	-	50	-	K/W

[2] Device mounted on an FR4 PCB, single-sided copper, tin plated and standard footprint.

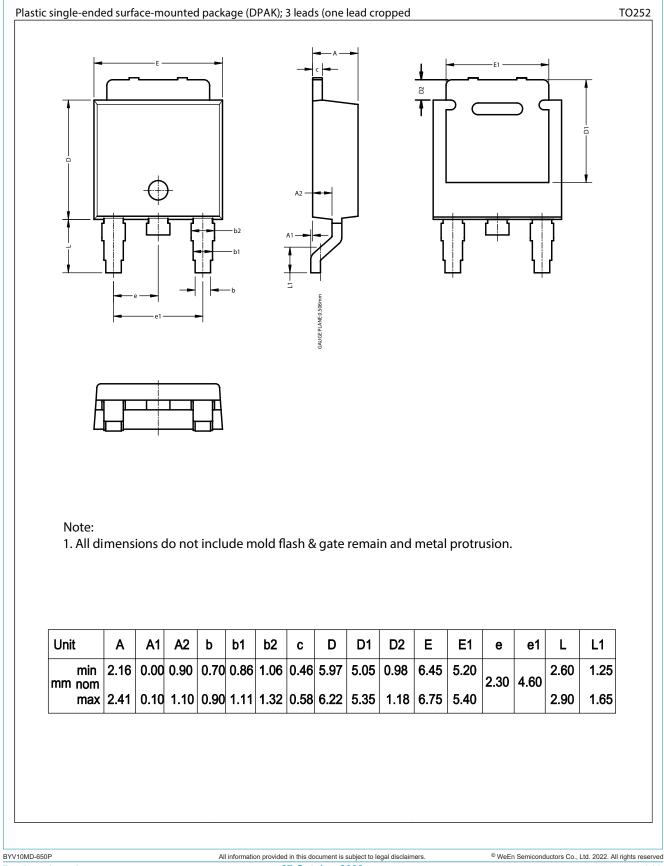


10. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
	aracteristics						
V _F	forward voltage	I _F = 10 A; T _i = 25 °C; <u>Fig. 6</u>		-	1.90	2.60	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.50	2.20	V
R	reverse current	V _R = 650 V; T _j = 25 °C		-	0.2	30	μA
		V _R = 650 V; T _j = 150 °C		-	0.05	0.8	mA
Dynamic	characteristics						
Q _r	reverse charge	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_i = 25 \text{ °C}; \text{ Fig. 7}$		-	85	-	nC
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_i = 125 \text{ °C}; Fig. 7$		-	220	-	nC
t _{rr}	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{rr} = 0.25 \text{ A}; T_j = 25 \text{ °C}$		-	25	-	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$		-	18	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$		-	55	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	95	-	ns
I _{RM}	peak reverse recovery currentnon-repetitive avalanche energy	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$		-	3	-	A
		$I_{F} = 10 \text{ A}; V_{R} = 200 \text{ V}; \text{ d}I_{F}/\text{d}t = 200 \text{ A}/\mu\text{s}; T_{j} = 125 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$		-	4.7	-	A
as	non-repetitive avalanche energy	T _{j(init)} = 25 °C		7.5	-	-	mJ



11. Package outline



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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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